

A SCALING APPROACH FOR INTERACTING QUANTUM WIRES -A POSSIBLE EXPLANATION FOR THE 0.7 ANOMALOUS CONDUCTANCE

D. Schmeltzer¹ and A. Kuklov²

¹ *Physics Department at the City College of the CUNY,*

² *Physics Department at the College of Staten Island of the CUNY*

Abstract

We introduce a combined scaling and bosonization with zero modes approach to investigate a finite Quantum wire in thermal contact with the electronic gates. We consider the $4K_F$ scattering processes induced by the momentum transfer to the high energy electrons present in an wire with a transversal width d . It is found that at low electronic density the single particle self energy is comparable to the Fermi energy. This is caused by the $4K_F$ processes which renormalizes strongly the single particles excitation in the interacting wire. When a drain-source voltage is coupled adiabatically to the wire, the single particle self energy affects the conductance. We believe that the 0.7 conductance anomaly occurs when the renormalized Fermi energy, the temperature and the $4K_F$ Wigner crystal-type density modulation amplitude are comparable.

I. INTRODUCTION

The anomalous conductance $G \approx 0.7 \times (2e^2/h)$ observed by Pepper [6] and more recently by [7, 15] is one of the major unexplained effects in quantum wires. A number of theories have been proposed: Kondo Physics [8, 13] spin polarization [10, 14], formation of bound states [15], Wigner crystal [11, 21] and ferromagnetic zigzag structure in a Wigner crystal [12] but no consensus has been reached.

For noninteracting spin unpolarized electrons the conductance of a narrow ballistic quantum wires connected to two (large) reservoirs is quantized in units of $2e^2/h$. Early suggestions were that the electron-electron interaction should modify the conductance for a Luttinger liquid [4],[5] as $K(2e^2/h)$ where K is interaction-dependent. It, however, has been shown that in the case when electron-electron interaction in the leads is negligible the interactions in the wire will not modify the metallic conductance from $G = \frac{2e^2}{h}$ [2, 3]. This result was obtained for infinitely long wires where one takes first the frequency limit $\omega \rightarrow 0$ before the momentum limit $q \rightarrow 0$.

We will compute the conductance for a finite interacting wire at low electronic densities. This calculation will be performed in two steps : a) Compute the single particle spectrum of an interacting wire in thermal contact with the gates. b) Couple adiabatically the wire to the leads and compute the current.

Computation of the single particle spectrum: The repulsive electron-electron (e-e) interaction contains two parts the short range Hubbard and the long range Coulomb interaction. At low electronic densities the Coulomb interaction gives rise to density-density correlation function which exhibits $4K_F$ oscillations showing an incipient of charge density wave at a wave vector $4K_F$ [1]. This phenomena was coined the *quasi* Wigner crystal characterized by an almost periodic structure with the interparticle distance $r_{e-e} = \frac{1}{n_e}$.

We include in our calculation the $4K_F$ e-e umklapp interaction in the lowest electronic band induced by the charge excitations in the upper bands present in a wire of width d . Only at distances $x > d$ we can use an effective one dimensional model. This model is found by projecting out high energy bands.

The short distance cut-off allows to map the interacting model to an effective lattice model with the lattice constant d which replaces the microscopic lattice constant a . There-

fore the umklapp momentum $G^{(d)} = \frac{2\pi}{d}$ is provided by the high energy electrons. For such a lattice periodicity we expect a strong $4K_F$ scattering at electronic densities $4K_F \approx G^{(d)}$. The effect of umklapp term generated by the finite width d has not been consider before. From the experimental data [7] we observe that for the Fermi momentum which corresponds to the voltage -5.1 volt the bias phase is $4K_F(V_G)d \approx \pi$. For such a phase the $4K_F$ scattering processes are negligible, this is seen in the experiment as an ideal conductance $G = \frac{2e^2}{h}$.

We propose that the conductance dependence on the gate voltage can be explained by studying effect of the e-e interactions on the bias term $4K_F(V_G) - G^{(d)}$. The missing umklapp momentum is supplied by the scattering of of the electron by the electrons in the upper bands . When the density is reduced the long range Coulomb interactions enhances the the umklapp $4K_F$ scattering channel giving rise to strong single particles (positive) self energy corrections which ultimately develop into a quasi Wigner crystal gap at extremely low densities. This self energies renormalizes the single particles energies . The fixed chemical potential dictated by the gates causes the system to become insulating when the chemical potential is comparable to the self energy renormalizations.

When we couple the wire to the leads we observe that the formation of the quasi gap at extremely low densities gives rise to the 0.7 conductance anomaly when the temperature T , Fermi temperature T_F and the quasi gap temperature T_{gap} (controlled by the gate voltage) are comparable.

The conductance is given by:

$$G = \frac{2e^2}{h} f_{F.D.} \left[\frac{-\epsilon_F(V_G) + \delta\Sigma(V_G, l(V_G), T)}{K_B T} \right] - f_{F.D.} \left[\frac{\epsilon_F(V_G) + \delta\Sigma(V_G, l(V_G), T)}{K_B T} \right]$$

where $\epsilon_F(V_G)$ is the Fermi energy which is determined by the gate voltage and $\delta\Sigma(V_G, l(V_G), T)$ is the self energy .

The plan of this paper is as followings: In chapter II we present the interacting Fermion model. In order to study the renormalization effects of the finite wire it is advantageous to work with an equivalent Bosonic model. In order to have a full Fermionic Bosonic representation we will include the zero modes [2, 13]. The inclusion of the zero modes is essential for finite wires with long range interaction since the level spacing is enhanced by the interactions. In chapter III we present the Renormalization Group (R.G.) analysis and show that the scaling of the bias term allows to investigate the effect of the gate voltage on the $4K_F$ scattering processes. We show that presence of the image charges in the gates screen

the long range potential and therefore the renormalized effective Luttinger interaction parameter is changed to: $K_{eff.}(l) = \frac{K_R(l)}{\sqrt{1+\alpha(\frac{c}{v_R(l)})\log(\frac{\xi}{d})^2}}$ where $l = l(V_G)$ is the scale dependence on the gate voltage, $\xi > d$ is the metallic screening length, L is the length of the wire and α is the fine structure constant which measures the strength of the long range interaction ($K_R(l)$, $v_R(l)$ are the renormalized Luttinger parameter with the initial value $K < 1$ [5] and Fermi velocity). We show that the inverse compressibility of the system $\frac{1}{\kappa} \propto \frac{1}{K_{eff.}^2(l)}$ has a minimum at low densities where the 0.7 structure is observed. In chapter IV we use the scaling equation and the zero mode interactions to compute the effective hamiltonian. Chapter V is devoted to the mapping of the Bosonic model back to a Fermionic hamiltonian using the the triple Jacoby identity [22]. We find that the single particle experience a positive self energy correction. In chapter VI we show that the effect of the interactions is to reduce the bias in a such a way that at extremely low density a quasi-gap is opened. In chapter VII we use the renormalized single particle spectrum to compute the conductance. In chapter VIII we present our conclusions and chapters IX, X and XI represents two appendixes.

II. THE MODEL

We will consider a finite wire with a finite width d at low electronic densities in the presence of the e-e interactions. The finite width defines the short distance cut-off for which an effective one dimensional model can be found. We will use the explicit dependence of the electronic density on the gate voltage given by [7]. The gate voltage will not enter explicitly in the calculations, instead we will use the density or the Fermi momentum implicit dependence. The parameter in the experiment were: the gate screening length $\xi = 10^{-7}m$, the wire length $L \approx 10^{-6}m$, the width $d \approx \frac{L}{100}$ and the two dimensional carrier density was $n_s \approx 2.5 \times 10^{11}cm^{-2}$. For $\xi > d$ the long range Coulomb interaction is given by: $V^{(c)}(|x|) = \frac{e^2}{\sqrt{x^2+d^2}} - \frac{e^2}{\sqrt{x^2+\xi^2}}$. The Fourier transform of this potential $V^{(c)}(q)$ is given given in terms of the $K_0(x)$ Bessel function which obey $K_0(x) \approx \text{Log}(1/x)$ when $x \rightarrow 0$:

$V^{(c)}(q) = 2e^2M(qd, q\xi) \equiv 2e^2(K_0(qd) - K_0(q\xi))$ The effect of the short range interactions will be described by a Hubbard model. For not to low densities the Hubbard model can

be represented in terms of a Bosonic charge H_c and spin density H_s hamiltonian. The hamiltonian takes the form $H = H_c + H_s$ with the charge K and spin stiffness K_s . At low density it is not possible to Bosonize directly the Hubbard model yet the description in terms of a charge H_c and spin excitations H_s hamiltonian is valid. From the Bethe ansatz [9] calculation one can replace the interacting fermions for any Hubbard interaction U at any electronic density n_e by an effective hamiltonian which is described by the charge and spin collective excitations. The parameters for this hamiltonian are known numerically : Charge parameter $K = K(U, n_e)$, Fermi velocity $v_F = v_F(U, n_e)$ and the $4K_F$ umklapp interaction $g = g(U, n_e) = \hat{g}\Lambda^2$ where Λ is the momentum cut-off $\Lambda = \frac{2\pi}{d}$.

For a wire of length $L \approx 10^{-6}m$ at a temperature $T \approx 1$ Kelvin it is useful to replace the interacting Fermionic model by the $1d$ Bosonic model. The advantage of Bosonization consist in the simplicity of the calculations. In order to compute the single particle excitations we need to refine the Bosonization method by incorporating Fermionic excitations. The Fermionic excitations will be incorporated using the zero modes [2, 13]. We introduce an extended Hilbert space given by $|N_{R,\sigma}; m_q \rangle \otimes |N_{L,\sigma}; m'_q \rangle$ where $m_q \geq 0$, $m'_q \geq 0$ are integers which specify the number of bosonic quanta (particles -holes excitations) with a momentum $q = \frac{2\pi}{L}n_q > 0$ and $\hat{N}_{R,\sigma}$, $\hat{N}_{L,\sigma}$ represent the change of the total number of electrons of the right and left ground states. The formal proof which relates the Fermionic occupation number to the **Zero mode operators** is given by the **triple product Jacoby identity** [22]. This identity allow us to describe the renormalized wire as a non interacting wire with renormalized energies.

In order to Bosonize the Fermion operators $\psi_\sigma(x)$ and $\psi_\sigma^+(x)$ we introduce the representation: $\psi_\sigma(x) = e^{iK_F x} R_\sigma(x) + e^{-iK_F x} L_\sigma(x)$

Where $K_F = K_F(V_G)$ is the Fermi momentum which depends on the external gate voltage V_G . Following [2, 13] we represent the right $R_\sigma(x)$ and left $L_\sigma(x)$ fermions operators in terms of the Bosonic -particle holes excitations $\Theta_{R,\sigma}(x) = \Theta_\sigma(x) - \Phi_\sigma(x)$, $\Theta_{L,\sigma}(x) = \Theta_\sigma(x) + \Phi_\sigma(x)$ and the zero mode coordinates $\alpha_{R,\sigma}, \alpha_{L,\sigma}$ with their canonical conjugate fermion number operators $\hat{N}_{R,\sigma}$, $\hat{N}_{L,\sigma}$ ($\sigma = \uparrow, \downarrow$). The physics of the zero modes is described in terms of the ground state charge operator $\hat{Q}_c = \sum_{\sigma=\downarrow, \uparrow} [\hat{N}_{R,\sigma} + \hat{N}_{L,\sigma}]$ and ground state current operator $\hat{J}_c = \sum_{\sigma=\downarrow, \sigma=\uparrow} [\hat{N}_{R,\sigma} - \hat{N}_{L,\sigma}]$. The zero modes obey the commutation rules $[\alpha_{R,\sigma}, \hat{N}_{R,\sigma'}] = i\delta_{\sigma,\sigma'}$, $[-\alpha_{L,\sigma}, \hat{N}_{L,\sigma'}] = i\delta_{\sigma,\sigma'}$ and $[\alpha_{R,\sigma}, \hat{N}_{L,\sigma'}] = [\alpha_{L,\sigma}, \hat{N}_{R,\sigma'}] = 0$.

The representation for the right and left mover fermions operators is given by:

$$R_\sigma(x) = \sqrt{\frac{\Lambda}{2\pi}} e^{i\alpha_{R,\sigma}} e^{i(2\pi/L)(\hat{N}_{R,\sigma}-1/2)x} e^{i\sqrt{4\pi}\Theta_{(R,\sigma)}(x)}$$

$$L_\sigma(x) = \sqrt{\frac{\Lambda}{2\pi}} e^{-i\alpha_{L,\sigma}} e^{-i(2\pi/L)(\hat{N}_{L,\sigma}-1/2)x} e^{-i\sqrt{4\pi}\Theta_{(L,\sigma)}(x)}$$

The fermion number operator $\hat{N}_{R,\sigma}$ and $\hat{N}_{L,\sigma}$ are defined with respect the free fermion momentum $K_F(V_G)$. Due to the e-e interactions the self energy will shift up the single particle energy in the wire .

(Following [7] the Fermi momentum has the gate voltage dependence: $K_F(V_G) = \frac{\pi}{2}n_e(V_G) = \frac{C_a}{e}(V_G - V^{th})$ for $V_G > V^{th} \approx -5.52\text{volt}$ where V^{th} is the gate voltage at which the wire is pinched of and the constant $\frac{C_a}{e}$ has the value $\frac{C_a}{e} = 1.2 \cdot 10^8(\text{Volt} \cdot \text{meter})^{-1}$.)

The gate voltage is in thermal contact with the wire and determines the number of electrons in the wire measured by the Fermi energy $\epsilon_F(V_G)$. The presence of the e-e interaction shifts up the single particle energies by $\delta\Sigma(V_G, l(V_G))$ given in appendix B. In the absence of interactions the single particle energy $\epsilon(n)$ at $T = 0$ in the ground state are restricted to $-\epsilon_F(V_G) < \epsilon(n) \leq 0$. The e-e interactions shifts up the spectrum to $E(n) = \epsilon(n) + \delta\Sigma(V_G, l(V_G))$ restricting the single particles energy in the ground state to: $-(\epsilon_F(V_G - \delta\Sigma(V_G, l(V_G)))) < E(n) \leq \delta\Sigma(V_G, l(V_G))$. The wire will be metallic if the Fermi energy is larger than the self energy, $\epsilon_F(V_G) > \delta\Sigma(V_G, l(V_G))$.

At some time $t = -\infty$ the wire is decoupled from the leads and contains an electronic density $n_e(V_G)$ which is related to V_G . Due to the e -e interactions the single particle energies will be modified from $\epsilon(n)$ (where n is the discrete momentum $k = \frac{2\pi}{L}n$) to $E(n) = \epsilon(n) + \delta\Sigma(V_G, l(V_G))$. Only at a time $t = 0$ the wire is coupled to the leads. Here the assumption is that the coupling is done adiabatically such that the single electronic spectrum has not been much altered. (In reality the coupling to the leads will give rise to a broadening of the original single particle energy in the wire but the effect on the self energy $\delta\Sigma(V_G, l(V_G))$ computed in the absence of leads will be only slightly modified .)

In the first part we present the calculation in the absence of the leads. For each right and left mover in the wire we consider a parabolic single particle dispersion $\epsilon(n)$ where n is the discrete momentum $k = \frac{2\pi}{L}n$. We introduce the right and left single particle dispersion $\epsilon_R(m) = \epsilon(n = n_F + m)$, $\epsilon_L(m) = \epsilon(n = -n_F + m)$ where $-n_F \leq m \leq n_F$. The value of n_F is a function of the gate voltage and is defined according to the relation $K_F(V_G) = \frac{2\pi}{L}n_F(V_G)$. The single particle excitations will be restricted to a finite band width $-\epsilon_F(V_G) \leq \epsilon_{R,L}(m) \leq \epsilon_F(V_G)$ where $\epsilon_F(V_G) = \frac{\hbar^2 K_F^2(V_G)}{2m^*}$ is the Fermi energy .

We introduce the normal order with respect the non-interacting ground state $|F\rangle$ (see

Appendix A). For any operator A we have, $: A : \equiv A - \langle G|A|G \rangle$. Due to interactions we expect to find that a wire of length L at a temperature T will be described by a new ground state $|G \rangle$ which is shifted by $\delta\Sigma(V_G, l(V_G), T)$ with respect the non-interacting ground state $|F \rangle$. The normal order $\hat{N}_{R,\sigma} \hat{N}_{L,\sigma} \hat{N}_{R,\sigma} \equiv: N_{R,\sigma} :$ and $\hat{N}_{L,\sigma} \equiv: N_{L,\sigma} :$ are given in the Appendix A.

We bosonize the hamiltonian H . This is done by introducing linear single particle excitations around the Fermi energy. We restrict the single particles spectrum by the momentum cut-off $\pm \frac{2\pi}{L} n_F(V_G) \approx \pm \Lambda$ and obtain the *Bosonic* representation for the interacting *fermionic* system:

$$H = H_c^{n \neq 0} + H_s^{n \neq 0} + H^{n=0} \quad (1)$$

The first two hamiltonians $H_c^{n \neq 0} + H_s^{n \neq 0}$ represent the particle hole excitations and $H^{n=0}$ represents the zero modes. The charge excitations $H_c^{n \neq 0}(\Theta, \Phi)$ are given in terms of the bosonic fields $\Theta = \frac{\Theta_{\uparrow} + \Theta_{\downarrow}}{\sqrt{2}}$, $\Phi = \frac{\Phi_{\uparrow} + \Phi_{\downarrow}}{\sqrt{2}}$:

$$\begin{aligned} H_c^{n \neq 0}(\Theta, \Phi) = & v\hbar \left[\int_{-L/2}^{L/2} dx \left[\frac{K}{2} (\partial_x \Phi(x))^2 + \frac{1}{2K} (\partial_x \Theta(x))^2 \right. \right. \\ & \left. \left. + g \cos[\sqrt{8\pi}\Theta(x) + \hat{\alpha} + (4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)x] \right] \right. \\ & \left. + \frac{e^2}{\pi\kappa} \int_{-L/2}^{L/2} \int_{-L/2}^{L/2} dx dx' \partial_x \Theta(x) \left[\frac{e^2}{\sqrt{(x-x')^2 + d^2}} - \frac{e^2}{\sqrt{(x-x')^2 + \xi^2}} \right] \partial_{x'} \Theta(x') \right] \quad (2) \end{aligned}$$

where the Fermi velocity v and the Luttinger parameter K are related by the relation: $vK = v_F = \frac{\hbar K_F(V_G)}{m^*}$. The umklapp interaction given by $\cos[\sqrt{8\pi}\Theta(x) + \hat{\alpha} + (4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)x]$ and $\hat{\alpha} = \sum_{\sigma=\uparrow,\downarrow} [\alpha_{R,\sigma} + \alpha_{L,\sigma}]$. represent the effective interaction obtained by integrating out upper bands. As a result the effective interaction derived by the projection of the upper bands will have a short distance cut-off d . This can be taught as an effective lattice spacing d (the width of the wire). For a periodic lattice with the lattice spacing d we will have that $4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c$ is equivalent to: $4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c + \frac{2\pi}{d}$.

The average electron-electron distance r_{e-e} gives rise to the the Wigner crystal momentum $G^{(Wigner)} \equiv \frac{2\pi}{r_{e-e}}$ modulation for the electronic ground state. For a periodic lattice with spacing d the umklapp momentum $G^{(d)} \equiv \frac{2\pi}{d}$ provided by the collective high energy electrons

in finite width wire guarantees the momentum conservation. For such a periodic finite wire a violation of the conservation of momentum by the bias term $G^{(Wigner)} - G^{(d)} \neq 0$ is allowed. We will limit ourself to relative low densities for which the condition $G^{(d)} > G^{(Wigner)}$ is obeyed. For the remaining part the analysis will be performed for a continuous model with a short distance cut-off d . The derivation of the $4K_F$ scattering term is given in appendix C.

The spin density excitations given by the hamiltonian $H_s^{n \neq 0}(\Theta_s, \Phi_s)$ will be ignored in the absence of a magnetic field.

The zero mode hamiltonian $H^{n=0}$ is given by:

$$\begin{aligned}
: H^{(n=0)} : &= \frac{\hbar v_F}{2L} [\hat{N}_{R,\sigma=\uparrow}^2 + \hat{N}_{L,\sigma=\uparrow}^2 + \hat{N}_{R,\sigma=\downarrow}^2 + \hat{N}_{L,\sigma=\downarrow}^2] + \\
&u^{(B)}(L) : [(N_{R,\sigma=\uparrow} + N_{L,\sigma=\uparrow}) + (N_{R,\sigma=\downarrow} + N_{L,\sigma=\downarrow})]^2 : - \\
&u^{(S)}(L) : [(N_{R,\sigma=\uparrow} + N_{L,\sigma=\uparrow})^2 - (N_{R,\sigma=\downarrow} + N_{L,\sigma=\downarrow})^2] : + \\
&\frac{e^2}{\kappa_0} \frac{1}{2L} F\left(\frac{L}{d}, \frac{\xi}{d}\right) : [(N_{R,\sigma=\uparrow} + N_{L,\sigma=\uparrow}) + (N_{R,\sigma=\downarrow} + N_{L,\sigma=\downarrow})]^2 : \quad (3)
\end{aligned}$$

The interactions $: H^{(n=0)_{int}} :$ are given in terms of the full non-normal order operators and $: H^{(n=0)_{int}} := H^{(n=0)_{int}} - \langle F | H^{(n=0)_{int}} F \rangle$. $u_R^{(B)}(L) = \frac{\hbar v_F}{2L} \left(\frac{1-K_R^2}{K_R^2}\right)$ is the renormalized backward interaction and $u_R^{(S)}(L) = \frac{\hbar v_F}{2L} \left(\frac{1-K_S^2}{K_S^2}\right)$ is the spin interaction controlled by $K_{S,R} \approx 1$ [2, 5].

The long range interaction for the zero mode is given by $F\left(\frac{L}{d}, \frac{\xi}{d}\right)$:

$$F\left(\frac{L}{d}, \frac{\xi}{d}\right) = \log\left[\frac{\sqrt{[1 + (\frac{d}{L})^2] + 1}}{\sqrt{[1 + (\frac{d}{L})^2] - 1}}\right] - \log\left[\frac{\sqrt{[1 + (\frac{\xi}{L})^2] + 1}}{\sqrt{[1 + (\frac{\xi}{L})^2] - 1}}\right] \quad (4)$$

The effective zero mode hamiltonian is obtained by integrating out the charge and spin density wave hamiltonian $H_c^{(n \neq 0)} + H_s^{(n \neq 0)}$. The integration is performed with the help of the Renormalization Group method. Therefore we have to compute the renormalized hamiltonian at the scale $l_L = \text{Log}[L/a^{(new)}]$. As a result the coupling constant of the hamiltonian will be replaced by $K \rightarrow K_R(l_L)$, $v_F \rightarrow v_R(l_L)$ and $g \rightarrow g_R(l_L)$. In addition the bias term $(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)$ will be replaced by $(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)e^{l_L}$. As a result of the e-e interactions we will replace the bias term $(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)$ by the expectation value with respect the true ground state (the shifted ground state) $|G \rangle$. We find that: $4K_F(V_G) + \frac{2\pi}{L} \langle \hat{Q}_c(V_G, T) \rangle \equiv 4K_F^{eff}(V_G)$. Following [7] we know that at the Voltage $V_G^{(0)} \approx -5.1 \text{ volt}$ the conductance is ideal, therefore we can assume that the umklapp term

is negligible. We will show that $4K_F^{eff}(V_G^{(0)})$ corresponds to the momentum $\frac{\pi}{d}$ and therefore $g(V_G^{(0)})$ can be neglected. Following [17] we do not neglect the original umklapp interaction for gate voltages $V_G < V_G^{(0)}$. Instead we scale down the model to a length scale $l = l(V_G)$ which obey the equation $4K_F^{eff}(V_G)e^{l(V_G)} = 4K_F^{eff}(V_G^{(0)})$. This equation define the scale $l = l(V_G) = \log\left[\frac{4K_F^{eff}(V_G^{(0)})}{4K_F^{eff}(V_G)}\right] \approx \log\left[\frac{4K_F(V_G^{(0)})}{4K_F(V_G)}\right]$ for which the renormalized umklapp interaction can be neglected. As a result the hamiltonian at the length scale l will depend on the renormalized parameters $K_R(l)$, and $v_R(l)$ where $l = \text{minimum}[L, l(V_G)]$

III. THE RENORMALIZATION GROUP EQUATIONS

Using the hamiltonian R.G. method introduced in [16] we have derived the R.G. equations for the model in eq.1 which in the absence of the Coulomb interaction are equivalent to the classical two dimensional Sine-Gordon. According to [19, 20] the system is gapless for $K > 1$ and has a gap for $K < 1$. The presence of the long-range interaction modifies in a significant way the results. (The long range interaction is controlled by the dimensionless coupling constant $\alpha = \frac{e^2}{\hbar c} \cdot \frac{1}{\kappa_0}$, light velocity c and dielectric constant for GaAs $\kappa_0 = 13.18$.) One finds [21] that for the case $4K_F(V_G) = \frac{2\pi}{d}$ the system is always gaped independent on the value K !

The gate screening plays a significant role therefore we will include this effect into the new R.G. equations. According to [16] the R.G. differential equation are obtained by projecting out the boson in the momentum shell $d\Lambda = \frac{d\Lambda}{\Lambda}$. Under the R.G. transformation we have a running cut-off $\Lambda(l) = \Lambda e^{-l}$. In the presence of the gate screening length scale $\frac{\xi}{d}$ and a bias term $(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)$ the new R.G. equations become:

$$(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c) \rightarrow (4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)e^l \quad (5)$$

$$\frac{d\hat{g}_R(l)}{dl} = 2\hat{g}_R(l)\left(1 - \frac{K_R(l)}{\sqrt{(1 + \alpha(\frac{c}{v_R(l)})M_R(l))}} - \frac{K_R^2(l)\hat{g}_R^2(l)}{4(1 + \alpha(\frac{c}{v_R(l)})M_R(l))}\right) \quad (6)$$

$$\frac{dK_R(l)}{dl} = -\frac{(K_R^3(l)\hat{g}_R^2(l))}{8(1 + \alpha(\frac{c}{v_R(l)})M_R(l))} \quad (7)$$

$$\frac{dv_R(l)}{dl} = \frac{v_R(l)K_R(l)^2\hat{g}_R^2(l)}{4(1 + \alpha(\frac{c}{v_R(l)})M_R(l))} \quad (8)$$

where the screening gate potential $M_R(l)$ has replaced the logarithmic function in [21]. $M_R(l)$ is given as a difference of two Bessel functions:

$$M_R(l) = 2(K_0[e^{-l}] - K_0[\frac{\xi}{d} \cdot e^{-l}]) \quad (9)$$

The solution of the R.G. equations depends on the initial values of the interaction parameters $\hat{g}_R(l=0)$, $K_R(l=0)$ and screening gate scale $\frac{\xi}{d}$.

For the repulsive interactions the effects of the screening due not change the qualitative behavior since $K < 1$. The screening controls the further decrease of K .

Here we will be study the case where $4K_F(V_G) < \frac{2\pi}{d}$. In order to compute the scaling functions we need to determine the relation between l and V_G . This is done using the fact that for $V_G^{(0)} = -5.1\text{volt}$ the conductance is given by $\frac{2e^2}{h}$ which the umklapp is exactly zero. The exact value of $l(V_G)$ is given in terms of the exact ground state $l(V_G) = \log[\frac{K_F^{eff}(V_G^{(0)})}{K_F^{eff}(V_G)}]$ which we approximate by $l(V_G) \approx \log[\frac{K_F(V_G^{(0)})}{K_F(V_G)}]$. We substitute the function $l(V_G)$ into the R.G. flow equations and find the R.G. equations as a function of the gate voltage V_G . Since the wire has a finite length L we stop scaling when l reaches the value $l = \text{minimum}[l(V_G), l_L]$. For initial conditions $K(0) = 0.98$, umklapp interaction $\hat{g}(0) = 0.05$ and screening ratio $\frac{\xi}{d} = 10$ we observe that with the decrease of the electronic density the Luttinger parameter $K_R(l(V_G))$ decreases. Including the effect of the Coulomb interactions replaces $K_R(l(V_G))$ by the effective interaction parameter $K_{eff.}(l(V_G))$.

Using the R.G. equation we obtain that the effective interaction parameter is given by:

$$K_{eff.}(l(V_G)) = \frac{K_R(l(V_G))}{\sqrt{1 + \alpha \cdot \frac{c}{v_R(l(V_G))} \cdot \log[\frac{\xi}{d}]^2}} \quad (10)$$

The effective interaction parameter $K_{eff.}(l(V_G))$ decreases monotonically with the decrease in the density and exhibit a maximum for densities where the 0.7 feature is observed. When the screening ratio approaches $\frac{\xi}{d} = 1$ this maximum is absent.

In figure 1 we have plotted the function $\frac{1}{K_{eff.}^2(l(V_G))}$ as a function of the gate voltage. We observe that $\frac{1}{K_{eff.}^2(l(V_G))}$ has a minimum for voltages which corresponds to the region where the 0.7 feature is seen. Since the compressibility $\kappa \propto K_{eff.}^2(l(V_G))$ we conclude that a possible maximum in the compressibility suggest the formation of a quasi gap. (Since the compressibility is proportional to the derivative of the renormalized chemical potential $\mu_R(V_G, l(V_G))$, $\frac{1}{\kappa} = (n_e(V_G))^2 \partial_{n_e(V_G)}[\mu_R(V_G, l(V_G))]$ we expect also minimum for the derivative.)

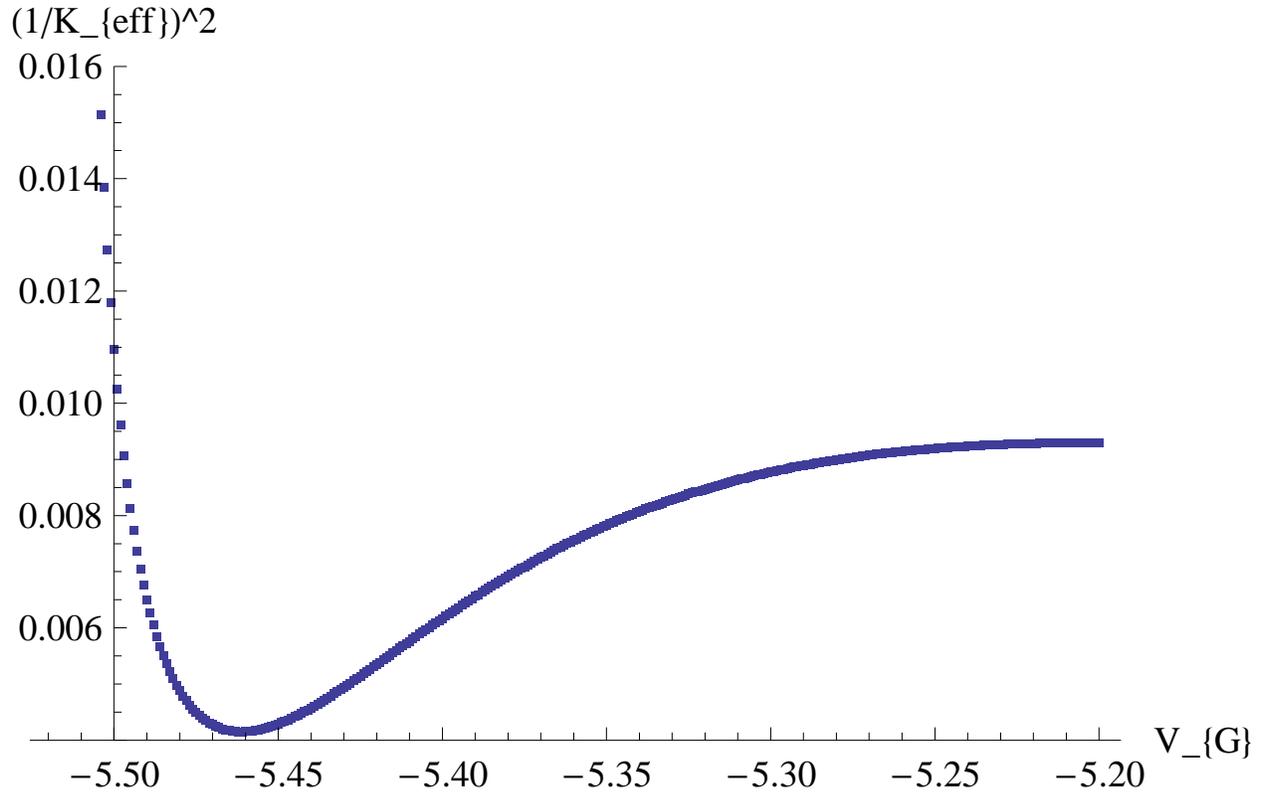


FIG. 1: The the effective parameter $\frac{1}{K_{\text{eff}}^2(l(V_G))}$ which is proportional to the inverse compressibility is plotted as a function of the gate voltage $l = l(V_G)$ for $L = 10^{-6}$ meter and screening ratio $\frac{\xi}{a} = 10$

IV. THE DERIVATION OF THE EFFECTIVE HAMILTONIAN

For Fermi momentum $K_F^{eff}(V_G) < K_F^{eff}(V_G^{(0)})$ the $4K_F$ umklapp will be present and will renormalize the interaction parameter. The value for which we can stop scaling and substitute $g(l(V_G)) \approx 0$ will be given by : $l(V_G) = \log[\frac{4K_F^{eff}(V_G^{(0)})}{4K_F^{eff}(V_G)}] \approx \log[\frac{4K_F(V_G^{(0)})}{4K_F(V_G)}]$. At the scale $b = e^{l(V_G)} < e^{L}$ the rescaled hamiltonian with $x = bx'$ will have the interaction parameters given by the R.G.equations with $g(l(V_G)) = 0$.

$$\begin{aligned}
H_{c,l}^{(n \neq 0)}[\Theta_R, \Phi_R] \approx & v_R(l) \hbar \left[\int_{-L/(2b)}^{L/(2b)} dx \left[\frac{K_R(l)}{2} (\partial_x \Phi_R(x))^2 + \frac{1}{2K_R(l)} (\partial_x \Theta_R(x))^2 \right] + \right. \\
& \left. \frac{e^2}{\pi \kappa} \int_{-L/(2b)}^{L/(2b)} \int_{-L/(2b)}^{L/(2b)} dx dx' \partial_x \Theta_R(x) \left[\frac{1}{\sqrt{(x-x')^2 + (\frac{d}{b})^2}} - \frac{1}{\sqrt{(x-x')^2 + (\frac{\xi}{b})^2}} \right] \partial_{x'} \Theta_R(x') \right]
\end{aligned} \tag{11}$$

The zero mode hamiltonian will depend on the renormalized coupling constant given by the R.G. equations (7),(8) and $g(l(V_G)) = 0$.

$$: H^{(n=0)}(l) :=: H_0^{(n=0)}(l) : + H_{int.}^{(n=0)}(l) : \tag{12}$$

The first term : $H_0^{(n=0)}(l)$: represents the non-interacting part:

$$: H_0^{(n=0)}(l) := \frac{\hbar v_F}{2L} [\hat{N}_{R,\sigma=\uparrow}^2 + \hat{N}_{L,\sigma=\uparrow}^2 + \hat{N}_{R,\sigma=\downarrow}^2 + \hat{N}_{L,\sigma=\downarrow}^2] \tag{13}$$

The second term represents the interactions : $H_{int.}^{(n=0)}(l)$: given as a function of the charge operator $Q_c = [(N_{R,\sigma=\uparrow} + N_{L,\sigma=\uparrow}) + (N_{R,\sigma=\downarrow} + N_{L,\sigma=\downarrow})]$ and the magnetization operator $Q_s = [(N_{R,\sigma=\uparrow} + N_{L,\sigma=\uparrow}) - (N_{R,\sigma=\downarrow} + N_{L,\sigma=\downarrow})]$.

$$: H_{int.}^{(n=0)}(l) := \eta_c(l(V_G)) : Q_c^2 : - \eta_s(l(V_G)) : Q_s^2 : \tag{14}$$

Where $\eta_c(l(V_G)) \equiv \frac{\hbar v_F}{2L} [(\frac{1-K_R^2(l(V_G))}{K_R^2 l(V_G)}) + \alpha(\frac{c}{v_F}) F(\frac{L}{de^{l(V_G)}}, \frac{\xi}{de^{l(V_G)}})]$ is the renormalized coupling constant for the charge-charge interactions and $\eta_s(l(V_G)) = \frac{\hbar v_F}{2L} (\frac{1-K_{S,R}^2(l(V_G))}{K_{S,R}^2 l(V_G)}) \approx 0$ is the effective coupling constant for the magnetic interactions . In both expressions the first term represents the short range-backward interaction and the second term given by the function $F(\frac{L}{de^{l(V_G)}}, \frac{\xi}{de^{l(V_G)}})$ represents the screened long range Coulomb interaction:

$$F\left(\frac{L}{de^{l(V_G)}}, \frac{\xi}{de^{l(V_G)}}\right) = \log\left[\frac{\sqrt{[1 + (\frac{de^{l(V_G)}}{L})^2] + 1}}{\sqrt{[1 + (\frac{de^{l(V_G)}}{L})^2] - 1}}\right] - \log\left[\frac{\sqrt{[1 + (\frac{\xi e^{l(V_G)}}{L})^2] + 1}}{\sqrt{[1 + (\frac{\xi e^{l(V_G)}}{L})^2] - 1}}\right] \quad (15)$$

Due to the fact that the zero mode component of the hamiltonian commutes the zero mode partition function can be computed exactly . Following the derivation given in appendix B we can replace the zero mode hamiltonian by an effective model (see Appendix B) :

$$\begin{aligned} : H^{(n=0)}(l)_{eff} : &\approx \frac{hv_F}{2L} [\hat{N}_{R,\sigma=\uparrow}^2 + \hat{N}_{L,\sigma=\uparrow}^2 + \hat{N}_{R,\sigma=\downarrow}^2 + \hat{N}_{L,\sigma=\downarrow}^2] \\ &\quad - \delta\Sigma(V_G, l(V_G)) [\hat{N}_{R,\sigma=\uparrow} + \hat{N}_{R,\sigma=\downarrow}] \\ &\quad - \delta\Sigma(V_G, l(V_G)) [\hat{N}_{L,\sigma=\uparrow} + \hat{N}_{L,\sigma=\downarrow}] \end{aligned} \quad (16)$$

where the explicit form of the self energy $\delta\Sigma(V_G, l(V_G))$ is given in the appendix B.

V. THE EFFECTIVE FERMIONIC MODEL FOR A WIRE OF LENGTH L

The static conductivity of the hamiltonian given in equation (1) can be study properties can be computed using the effective hamiltonian : $H^{(n=0)}(l)_{eff}$: given in equation (16). The static current does not couple to the particles holes excitations therefore we can ask what is the equivalent Fermionic hamiltonian which obeys the partition function identity:

$$T_r[e^{-\beta:H^{(n=0)}(l)_{eff}}: e^{-\beta:H_0^{(n\neq 0)}}:] \equiv T_r[e^{-\beta:H_{eff}^f}] \quad (17)$$

Where : $H_0^{(n\neq 0)}$: represents a free boson model (which does not affect the static conductance) and is given by :

$$: H_0^{(n\neq 0)} := v_F \hbar \left[\sum_{\sigma=\uparrow,\downarrow} \int_{-L/2}^{L/2} dx \left[\frac{1}{2} (\partial_x \Phi_\sigma(x))^2 + \frac{1}{2} (\partial_x \Theta_\sigma(x))^2 \right] \right] \quad (18)$$

According to the triple Jacoby identity [22] the trace on the right side dictate the form of the fermionic hamiltonian : H_{eff}^f : on the left side of the identity. We find the effective Fermionic hamiltonian:

$$: H_{eff}^f := \sum_{\sigma=\uparrow,\downarrow} \sum_{-n_F(V_G)}^{n_F(V_G)} [(\epsilon_R(m) + \delta\Sigma(V_G, l(V_G))) : R^+(m, \sigma) R(m, \sigma) :$$

$$+(\epsilon_L(m) + \delta\Sigma(V_G, l(V_G))) : L^+(m, \sigma)L(m, \sigma) :] \quad (19)$$

This effective hamiltonian will be used to compute the conductance.

VI. THE INDUCED CHARGE AND THE MODULATION OF THE FERMI SURFACE

According to the results given in equations (16), (19) and (37) in the appendix B we conclude that the single particle energies are shifted up in energy.

The wire is in thermal contact with the gates at a fixed chemical potential and therefore the positive shift in the single particle energy allows less level to be populated . As a result the electronic density is reduced in the wire. Using the the electronic density $n_e(V_G) = \langle F | \frac{Q_c}{L} | F \rangle$ dictated by the chemical potential in the gates we find that e-e interactions modifies the density to $\langle G | \frac{Q_c}{L} | G \rangle$ and at temperature T it is given by $\langle \frac{Q_c}{L} \rangle = \frac{n_e(V_G)}{\epsilon(V_G, l, T, L)}$. The bias term $(4K_F(V_G) + \frac{2\pi}{L}\hat{Q}_c)$ in equation (1) can be replaced by the true ground state expectation value (given in terms of the dielectric function $\hat{\epsilon}(V_G, l, T, L)$ given in equation (38)):

$$4K_F(V_G) + \frac{2\pi}{L} \langle G | \hat{Q}_c | G \rangle = 4K_F(V_G) + 2\pi [\langle G | \frac{Q_c}{L} | G \rangle - \langle F | \frac{Q_c}{L} | F \rangle] = \frac{4K_F(V_G)}{\hat{\epsilon}(V_G, l, T, L)} \equiv 4K_F^{eff}(V_G) \quad (20)$$

The assumption that for $V_G < V_G^{(0)}$ the scaling function $l(V_G)$ is determined by the equation $l(V_G) = \log[\frac{K_F^{eff}(V_G^{(0)})}{K_F^{eff}(V_G)}] = \log[\frac{K_F(V_G^{(0)})}{K_F(V_G)} \frac{\hat{\epsilon}(V_G, l(V_G), T, L)}{\hat{\epsilon}(V_G^{(0)}, T, L)}]$ can be checked . Using the width d as a short distance cut-off we compute the bias phase : $4K_F^{eff}(V_G)d$ Using the experimental value [7] $d = \frac{L}{100}$ we can check if the condition $\frac{4K_F^{eff}(V_G^{(0)} \approx -5.1 \text{ volt})}{d} \approx \pi$ is satisfied. In figure 2 we plot the function $\text{Cos}[4K_F^{eff}(V_G)d]$ and observe that that for the gate voltage $V_G \approx -5.1 \text{ volt}$ the phase of the *Cosine* is close to π justifying the use of this the point for defining a vanishing umklapp term in agreement with [17].

for voltages below -5.3 volt the *Cosine* is close to one pointing to an unbiased. We also confirm the condition that for the gate voltage $V_G \approx -5.1 \text{ volt}$ the phase of the *Cosine* is close to π justifying the use of this voltage as the point where the umklapp interaction vanishes. Therefore for any voltage below -5.1 volt we can use scaling.

In addition we compute the average effect of the bias on the umklapp interaction . We integrate over the full length of the wire and find that the bias term do not suppresses the umklapp interaction given in equation (1) for gate voltages below -5.4 volt. This effect is described by the function: $\frac{1}{L} \int_0^L \text{Cos}[4K_F^{eff}(V_G)x] dx = \frac{\text{Sin}(4K_F^{eff}(V_G)L)}{4K_F^{eff}(V_G)L}$ and is plotted in figure 3. The presence of the non vanishing umklapp interaction below -5.4volt suggest the possible formation of a quasi-Wigner crystal at low densities for a finite wire. With increasing the length of the wire the region of the Wigner crystal shrinks to zero.

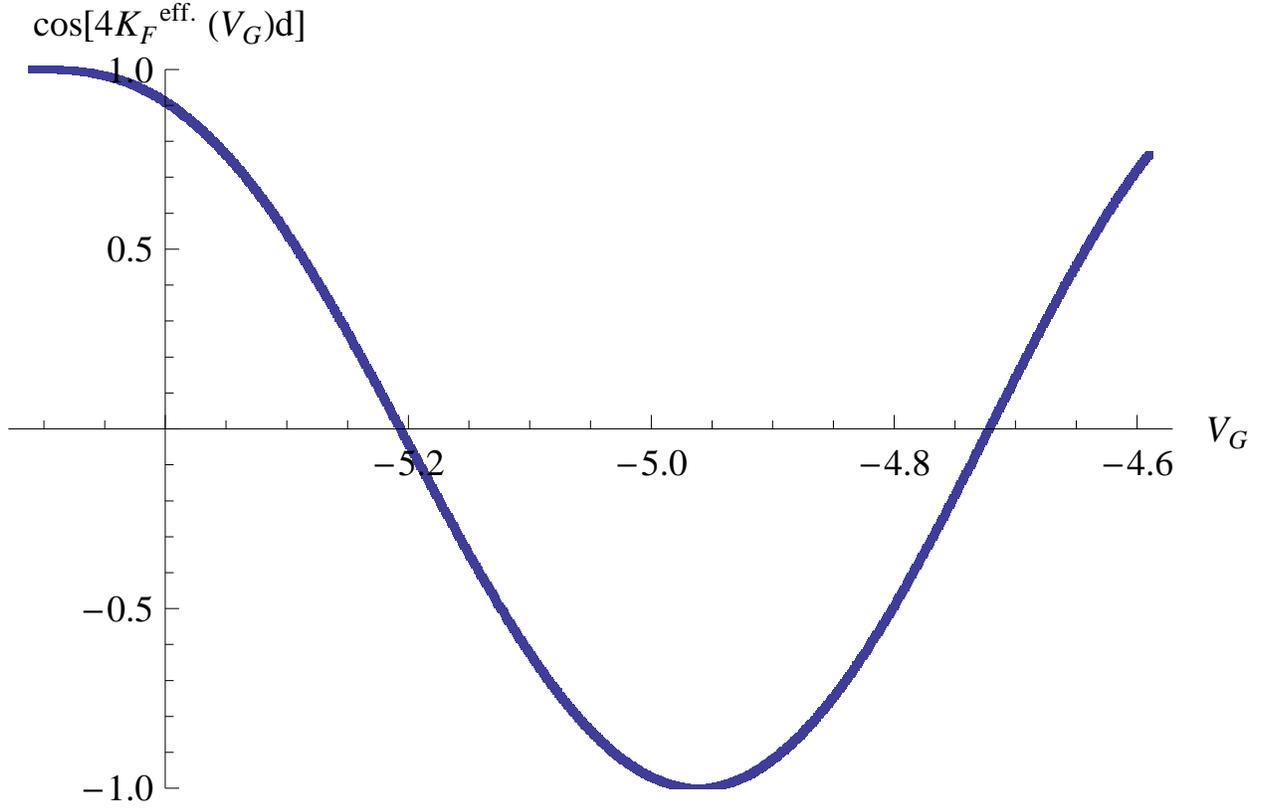


FIG. 2: The bias effect given by the cosine of the product Fermi momentum \times the lattice spacing $\text{Cos}[4K_F^{\text{eff.}}((V_G)d)]$ at ratio: $\frac{\xi}{d} = 10$. fixed temperature $T = 1 \text{ Kelvin}$, length $L = 10^{-6} \text{m}$ meter and interaction $K_R(l(0)) = 0.98$ where $d = \frac{L}{100} = 10^{-8} \text{m}$

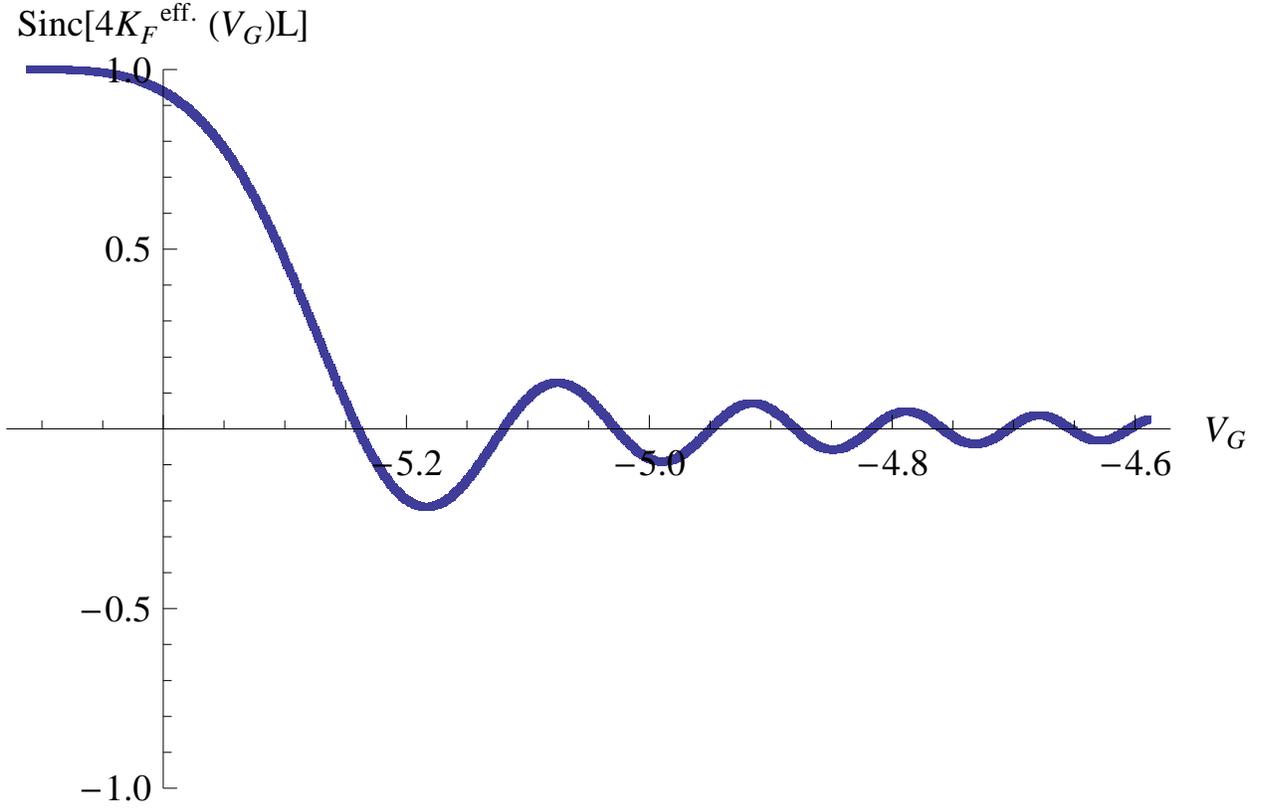


FIG. 3: The effective reduction of the umklapp interaction by the bias : $SinC[\frac{4K_F(l(V_G))}{\xi(V_G, l, T, L)}L]$ at ratio: $\frac{\xi}{l} = 10$. fixed temperature $T = 1$ Kelvin ,length $L = 10^{-6}$ meter and interaction $K_R(l(0)) = 0.98$

VII. COMPUTATION OF THE CONDUCTANCE USING THE EFFECTIVE FERMIONIC MODEL

The hamiltonian in equation (21) allows to identify the current operator \hat{I} . The explicit form of the current operator follows from the global $U(1)$ invariance for the right and left movers. One identified the current operator with the conserved $U(1)$ -*Noether* current.

$$\hat{I} = \frac{ev_F}{L} \sum_{\sigma=\uparrow,\downarrow} \sum_{m=-n_F(V_G)}^{m=n_F(V_G)} [L^+(m, \sigma)L(m, \sigma) - R^+(m, \sigma)R(m, \sigma)] \quad (21)$$

In order to compute the current we introduce a reservoir hamiltonian H_{Res} which describes the effect of the drain source voltage $V = \frac{\mu_L - \mu_R}{e}$.

$$H_{Res} = \sum_{\sigma=\uparrow,\downarrow} \sum_{m=-n_F(V_G)}^{n_F(V_G)} \left[\frac{eV}{2} (L^+(m, \sigma)L(m, \sigma) - R^+(m, \sigma)R(m, \sigma)) \right] \quad (22)$$

Under tis condition the steady state current will be determined by the partition function:

$$Z_f = T_r[e^{-\beta H_{eff}^f} e^{-\beta H_{Res}}] \quad (23)$$

In the second step we compute the thermal expectation function with respect the partition function Z_f and find for the current:

$$I = T_r[e^{-\beta H_{eff}^f} e^{-\beta H_{Res}} \hat{I}] [Z_f]^{-1} \quad (24)$$

As a result we obtain:

$$I = \frac{ev_F}{L} \sum_{\sigma=\uparrow,\downarrow} \sum_{m=-n_F(V_G)}^{m=n_F(V_G)} \left([f_{F.D.} \left[\frac{\epsilon_L(m) + \delta\Sigma(V_G, l(V_G)) + \frac{eV}{2} - \delta\mu_0(T)}{K_B T} \right]] - f_{F.D.} \left[\frac{\epsilon_R(m) + \delta\Sigma(V_G, l(V_G)) - \frac{eV}{2} - \delta\mu_0(T)}{K_B T} \right] \right) \quad (25)$$

We argue that by coupling adiabatically the leads to the wires the spectrum is not much modified. Under the condition of an ideal coupling (with almost zero reflectivity from the leads) the replacement of the leads hamiltonian with the thermal reservoir H_{Res} is justified. We anticipate that due to the non ideal coupling the single particle will have an energy broadening, but the effect on the self energy $\delta\Sigma(V_G, l(V_G))$ will be insignificant. Therefore

we will replace the discrete sum $\epsilon_{R,L}(m)$ by a continuum integration variable ϵ and take advantage of the cancelation of the velocity v_F by the density of states. Performing the integration with respect the energy variable ϵ and expanding with respect the voltage V gives the conductance $G = \frac{I}{V}$:

$$G \approx \frac{2e}{hV} \int_{-\epsilon_F(V_G)}^{\epsilon_F(V_G)} d\epsilon (f_{F.D.}[\frac{\epsilon + \delta\Sigma(V_G, l(V_G)) + \frac{eV}{2} - \delta\mu_0(T)}{K_B T}] - f_{F.D.}[\frac{\epsilon + \delta\Sigma(V_G, l(V_G)) - \frac{eV}{2} - \delta\mu_0(T)}{K_B T}]) \\ = \frac{2e^2}{h} (f_{F.D.}[\frac{-\epsilon_F(V_G) + \delta\Sigma(V_G, l(V_G)) - \delta\mu_0(T)}{K_B T}] - f_{F.D.}[\frac{\epsilon_F(V_G) + \delta\Sigma(V_G, l(V_G)) - \delta\mu_0(T)}{K_B T}]) \quad (26)$$

where $\delta\Sigma(V_G, l(V_G))$ is the self energy potential computed in Appendix B .

We observe that the self energy determines the conductance trough an effective chemical potential $\mu_R(V_G, l(V_G))$:

$$\mu_R(V_G, l(V_G)) = \epsilon_F(V_G) - \delta\Sigma(V_G, l(V_G)) \quad (27)$$

Equations 26 is are our central results for the conductance at finite temperatures and finite length. The accuracy of our result depends on the saddle point solution which becomes exact in the limit $\beta\eta_c(l(V_G)) \gg 1$ and is satisfied for our problem.

Using the experimental relation between the Fermi momentum and the gate voltage V_G given by [7] we have plotted the conductance in figures 4 and 5. In figure 4 we consider a typical screening ratio $\frac{\xi}{d} = 10$ and show the conductance for a varying range of temperatures 1 – 3 Kelvin.

Figure 5 shows the conductance at a fixed temperature $T = 1$ Kelvin for a variable range of screening ratios. We observe that when the $\frac{1}{r}$ interaction is completely screened $\frac{\xi}{d} = 1$ the 0.7 feature is absent.

In order to understand the effect of the self energy we plot in figure 6 the dependence of $\delta\Sigma(V_G, l(V_G))$ on the gate voltage V_G and in figure 7 we plot the renormalized chemical potential $\mu_R(V_G, l(V_G))$ defined in equation (27).

We observe that at low densities $\mu_R(V_G, l(V_G))$ vanishes . This means that the free energy has an extremum at a finite density. The chemical potential vanishes at the voltage $V_G^* > V^{th}$. For $V^{th} < V_G < V_G^*$ the renormalized chemical potential is negative indicating the formation of a quasi-gap.

In figure 7 we plot the function $\mu_R(V_G, l(V_G))$ and establish that the feature of 0.5 – 0.7 coincide with the position $V_G = -5.49$ Volt where the renormalized chemical potential

$\mu_R(V_G, l(V_G))$ changes sign. This result is due to the quasi-gap caused by the umklapp and long range interactions.

The conductance derivative is proportional to the renormalized chemical potential derivative which is related to the inverse compressibility $\frac{1}{\kappa(V_G)}$:

$$\frac{dG(V_G)}{dV_G} \propto \frac{d\mu_R(V_G, l(V_G))}{dV_G} \propto \frac{1}{n_s^2(V_G)\kappa(V_G)}$$

Therefore the *bump* around $V_G = -5.49$ Volt corresponds to the 0.7 anomaly is translated into a minimum for the conductance derivative $\frac{dG(V_G)}{dV_G}$. The compressibility $\kappa(V_G)$ is proportional to the inverse square of the effective interaction parameter $K_{eff.}(l(V_G))$ shown in figure (1). Therefore we have an additional confirmation for the formation of the quasi-gap.

In figure 8 we plot the function: $\frac{d\mu_R(V_G, l(V_G))}{dV_G}$. This function has a minimum at the voltage $V_G = -5.49$ Volt which corresponds to the 0.7 structure observed in the conductance graph.

VIII. CONCLUSIONS

We have shown that the partially screened long range interaction in the presence of the biased umklapp interaction is significant for the 0.7 feature. We believe that the appearance of this feature is related to a quasi-gap formation at low densities in finite wires. This feature is revealed in the effective chemical potential which his derivative with respect the gate voltage (or the inverse compressibility) has a minimum around $V_G = -5.49$ volt.

Acknowledgements

The authors want to acknowledge the financial support from the CUNY COLLABORATIVE GRANT award for the year 2008.

D.Shmeltzer wants to thank Dr.Jing Qiao Zhang for his help with respect the numerical part of this work based on programming with Mathematica.

D.Shmeltzer thanks Natan Andrei for explaining him his recent work.

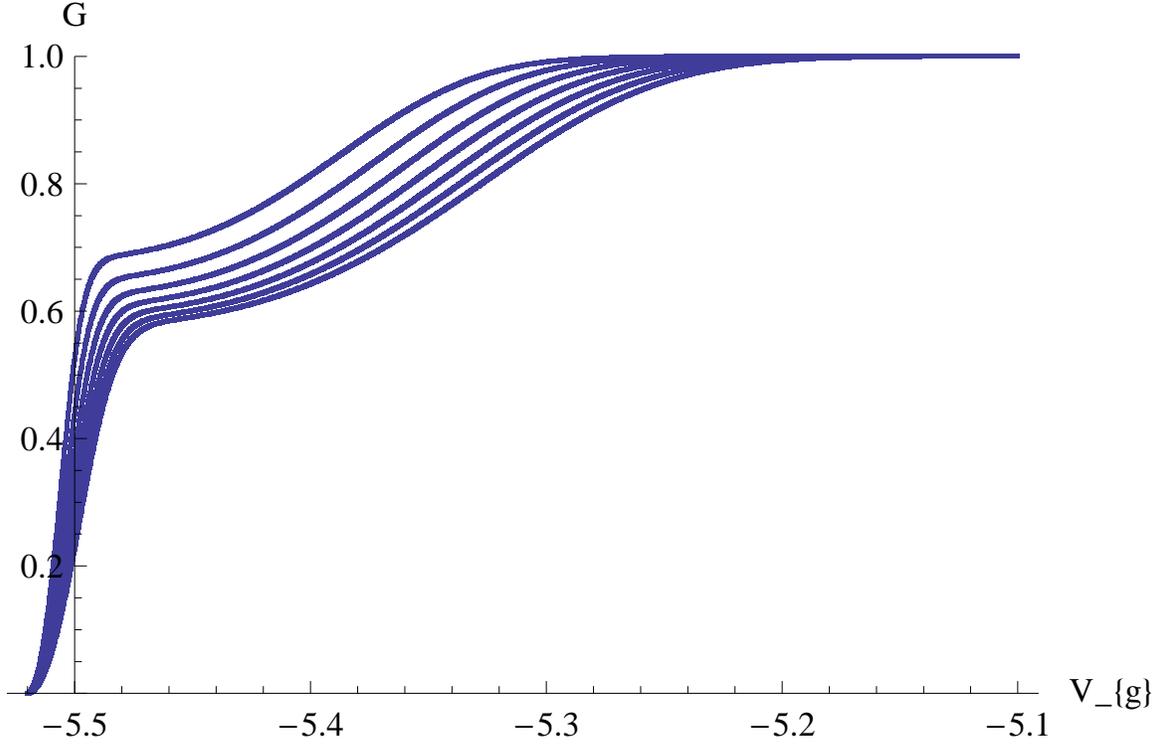


FIG. 4: The Conductance G in units of $\frac{2e^2}{h}$ as a function of the bias gate voltage $l = l(V_G)$ for the temperatures $T = 1.Kelvin$ (upper line) , $T = 1.25Kelvin$, $T = 1.5Kelvin$, $T = 1.75Kelvin$, $T = 2.0Kelvin$, $T = 2.25Kelvin$, $T = 2.5Kelvin$ and $T = 3.Kelvin$ (the lowest line) for umklapp parameter $g(l = 0) = 0.05$, $K(l = 0) \approx 0.98$, $L = 10^{-6}m$ meter and screening ratio $\frac{\xi}{d} = 10$

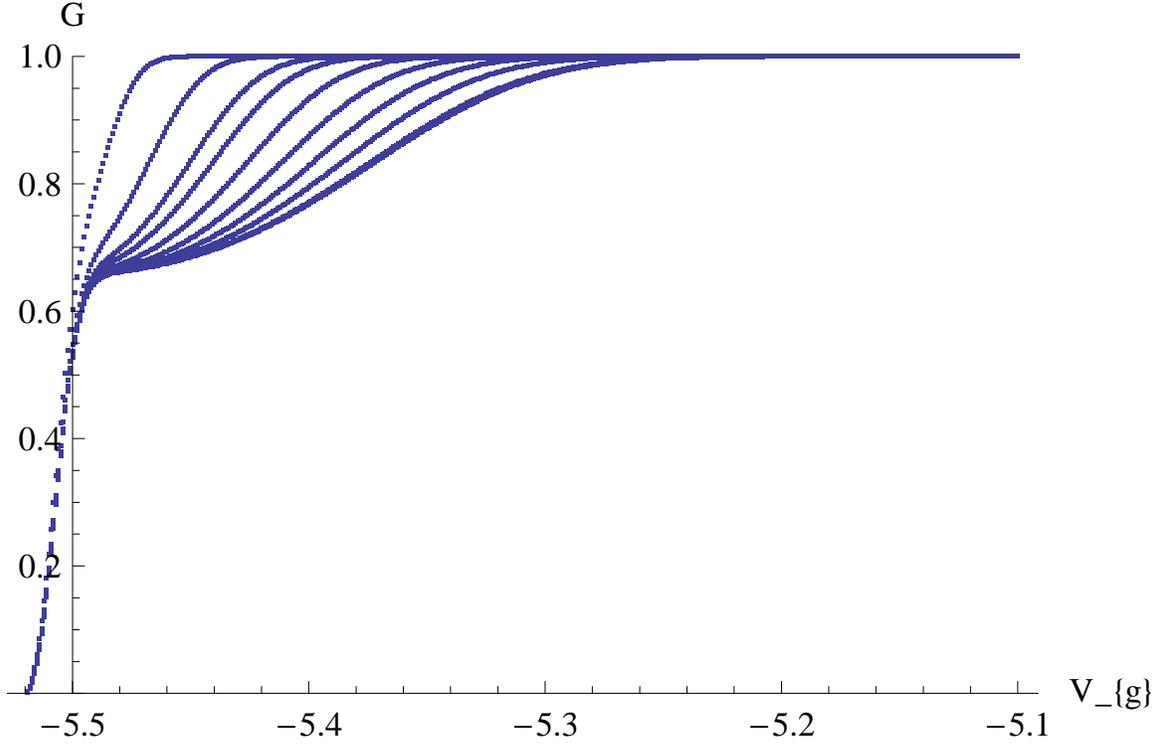


FIG. 5: The Conductance G in units of $\frac{2e^2}{h}$ for four screening ratios $\frac{\xi}{d} = 1$ (upper line), $\frac{\xi}{d} = 1.1$, $\frac{\xi}{d} = 1.3$, $\frac{\xi}{d} = 1.5$, $\frac{\xi}{d} = 2.$, $\frac{\xi}{d} = 3.$, $\frac{\xi}{d} = 5.$, $\frac{\xi}{d} = 10$, $\frac{\xi}{d} = 50$. and $\frac{\xi}{d} = 100$ at temperature $T = 1.Kelvin$ length $L = 10^{-6}m$ for the interactions parameters $\hat{g}_R(l = 0) = 0.05$, $K(l = 0) \approx 0.98$

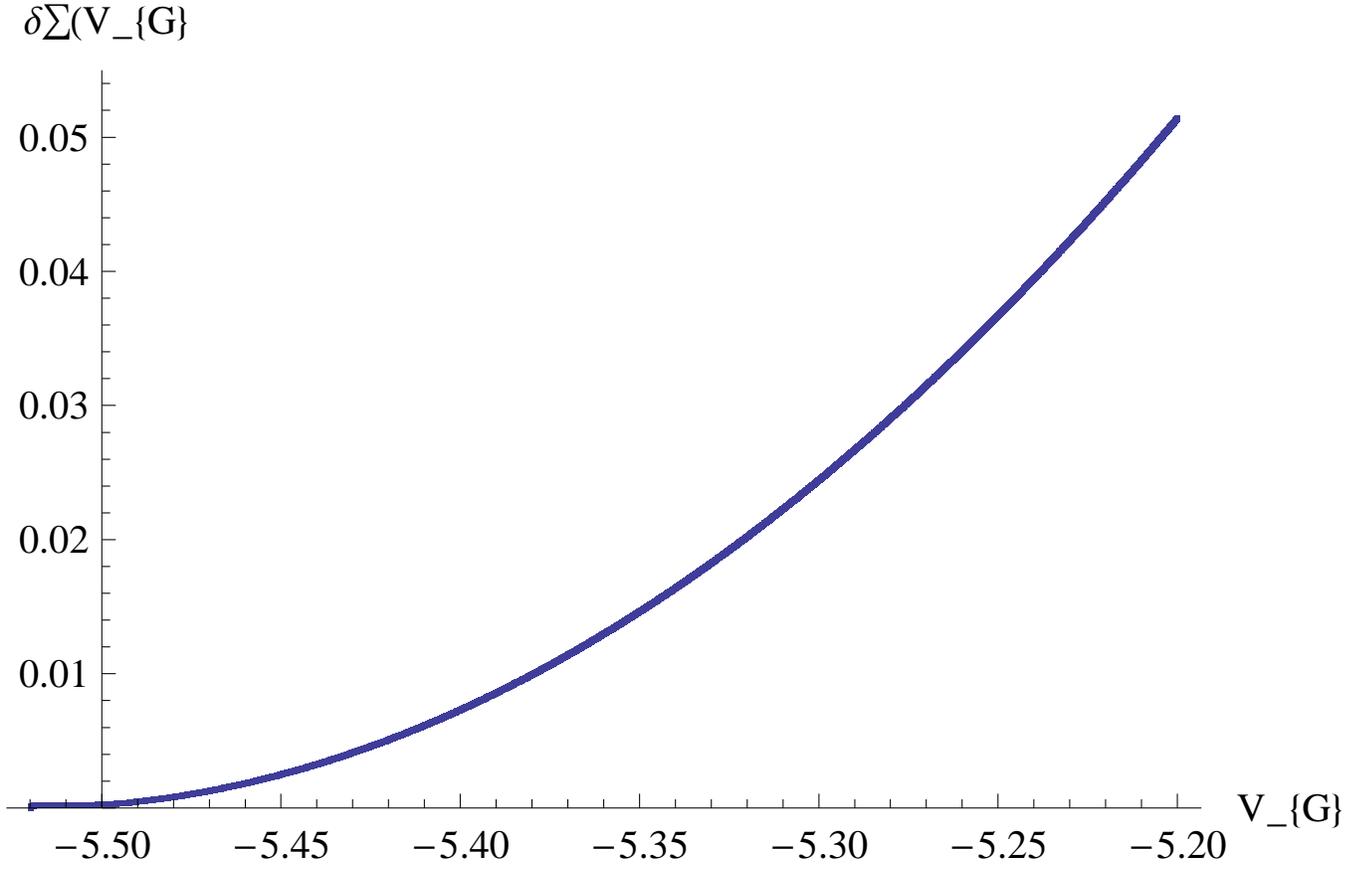


FIG. 6: The shift in the chemical potential $\delta\Sigma(V_G, l(V_G))$ for screening ratio $\frac{\xi}{d} = 10$ at temperature $T = 1.Kelvin$ length $L = 10^{-6}m$ for the interactions parameters $\hat{g}_R(l = 0) = 0.05$, $K(l = 0) \approx 0.98$

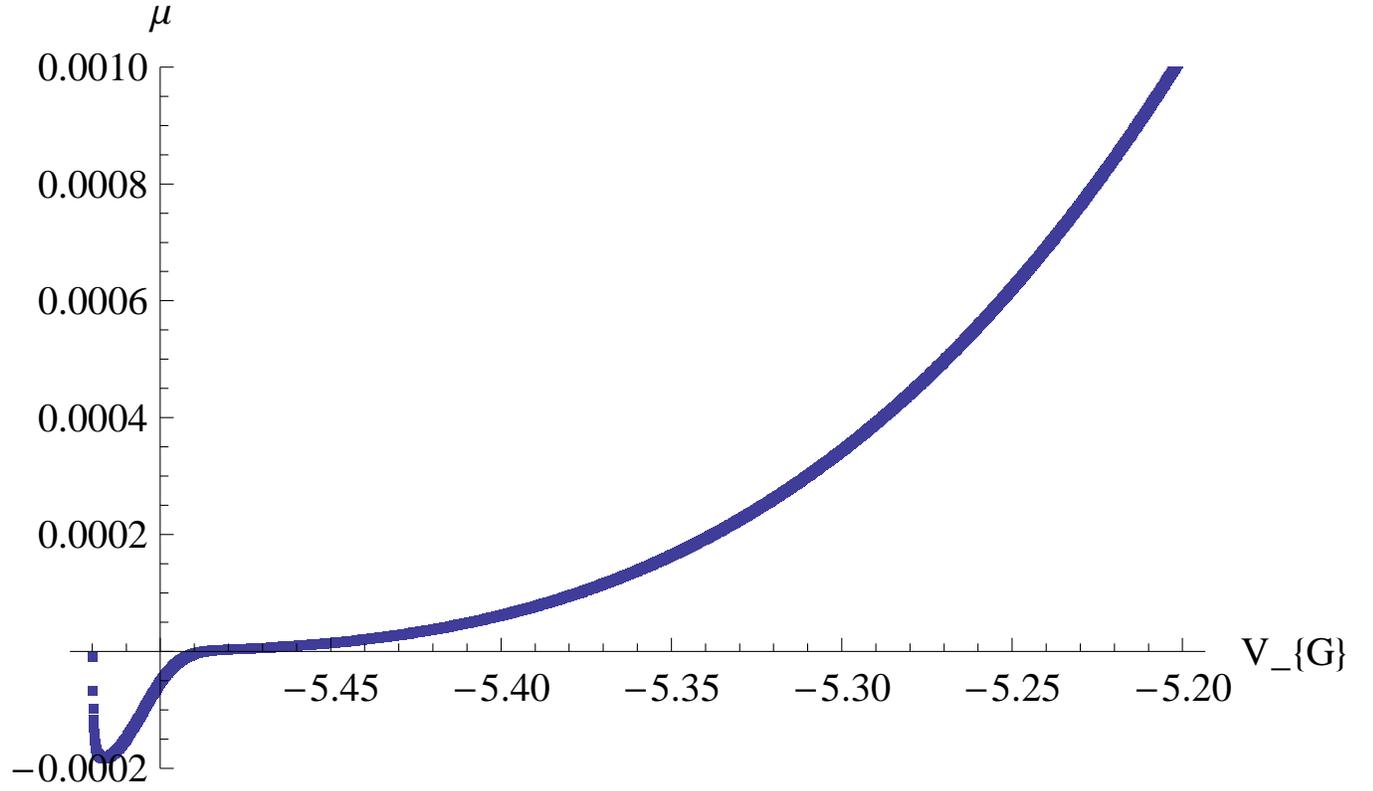


FIG. 7: The renormalized chemical potential $\mu_R(V_G, l(V_G))$ for screening ratio $\frac{\xi}{a} = 10$ at temperature $T = 1.Kelvin$ length $L = 10^{-6}m$ for the interactions parameters $\hat{g}_R(l = 0) = 0.05$, $K(l = 0) \approx 0.98$

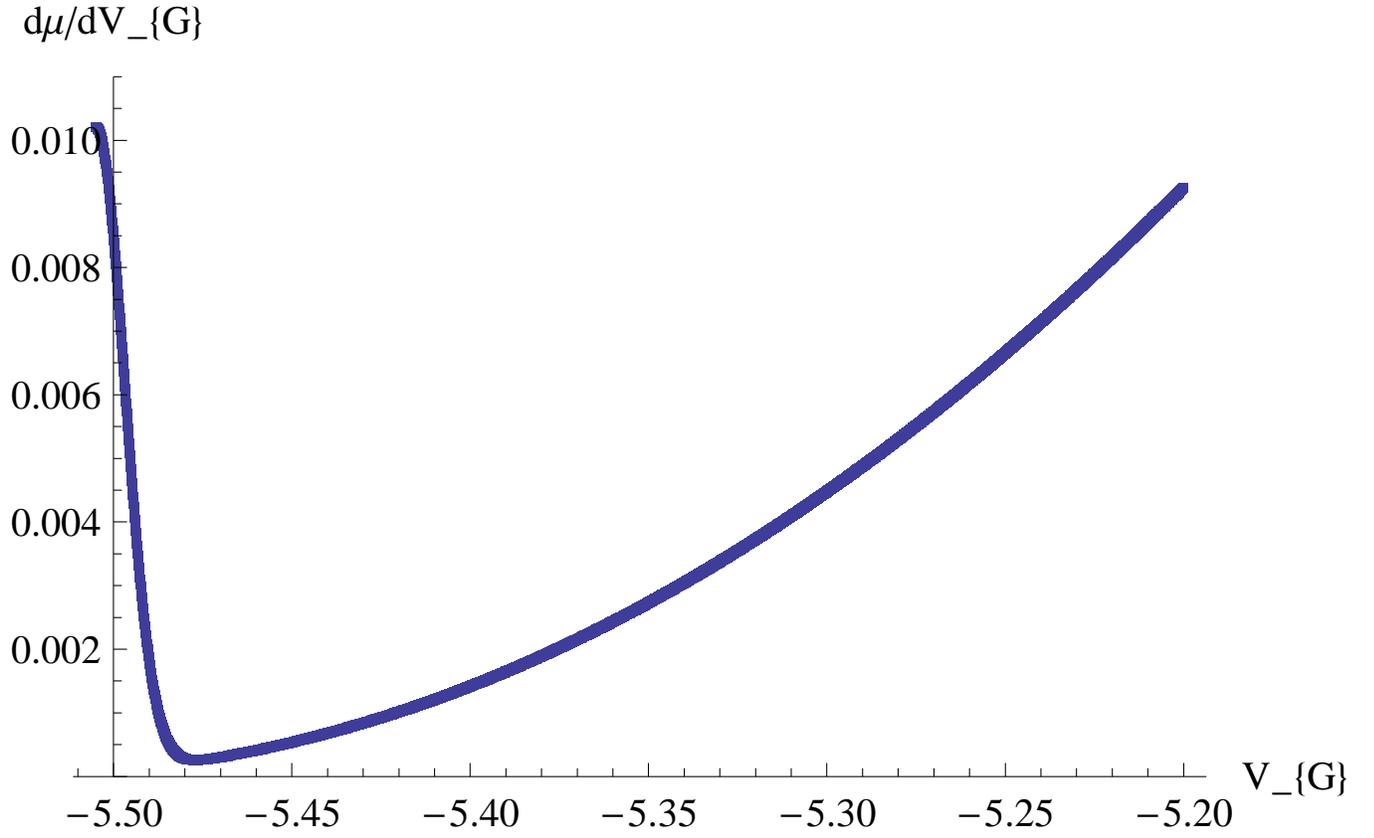


FIG. 8: The derivative of the chemical potential $\frac{d\mu_R(V_G, l(V_G))}{dV_G}$ for screening ratio $\frac{\xi}{d} = 10$ at temperature $T = 1.Kelvin$ length $L = 10^{-6}m$ for the interactions parameters $\hat{g}_R(l = 0) = 0.05$, $K(l = 0) \approx 0.98$

IX. APPENDIX-A

The ground state $|F\rangle$ is represented in terms of the empty particle state $|0\rangle$:

$$|F\rangle \equiv \prod_{\sigma=\uparrow,\downarrow} [\prod_{-n_F(V_G)}^{n_F(V_G)} R^+(m, \sigma) \prod_{n_F(V_G)}^{-n_F(V_G)} L^+(m, \sigma)] |0\rangle.$$

We introduce the symbols $\hat{N}_{R,\sigma}$ $\hat{N}_{L,\sigma}$ for the normal order at zero temperature $\hat{N}_{R,\sigma} \equiv: N_{R,\sigma} :$ and $\hat{N}_{L,\sigma} \equiv: N_{L,\sigma} :$. At finite temperature the normal order should be understood as a subtraction with respect the thermal ground state. We have: $\langle N_{L,\sigma}(\delta\mu_0(T), T) \rangle$, $\langle N_{R,\sigma}(\delta\mu_0(T), T) \rangle$ which replace the zero temperature subtraction $\langle F|N_{L,\sigma}|F\rangle$ and $\langle F|N_{R,\sigma}|F\rangle$

$$\hat{N}_{R,\sigma} = \sum_{-n_F(V_G)}^{n_F(V_G)} R^+(m, \sigma) R(m, \sigma) - \sum_{-n_F(V_G)}^{n_F(V_G)} \langle F|R^+(m, \sigma) R(m, \sigma)|F\rangle \equiv N_{R,\sigma} - \langle F|N_{R,\sigma}|F\rangle \quad (28)$$

and

$$\hat{N}_{L,\sigma} = \sum_{n_F(V_G)}^{-n_F(V_G)} L^+(m, \sigma) L(m, \sigma) - \sum_{n_F(V_G)}^{-n_F(V_G)} \langle F|L^+(m, \sigma) L(m, \sigma)|F\rangle = N_{L,\sigma} - \langle F|N_{L,\sigma}|F\rangle \quad (29)$$

In the presence of a thermal bath:

$$H_{Res} = \mu_R \sum_{-n_F(V_G)}^{n_F(V_G)} R^+(m, \sigma) R(m, \sigma) + \mu_L \sum_{-n_F(V_G)}^{n_F(V_G)} L^+(m, \sigma) L(m, \sigma) \quad (30)$$

with two chemical potentials μ_R and μ_L and temperature T we have:

$$\langle N_{R,\sigma}(V_G, \mu_R, T) \rangle = \sum_{n_F(V_G)}^{-n_F(V_G)} f_{F.D.} \left[\frac{\epsilon_R(m) - \mu_R - \delta\mu_0(T)}{K_B T} \right] \quad (31)$$

$$\langle N_{L,\sigma}(V_G, \mu_L, T) \rangle = \sum_{n_F(V_G)}^{-n_F(V_G)} f_{F.D.} \left[\frac{\epsilon_L(m) - \mu_L - \delta\mu_0(T)}{K_B T} \right] \quad (32)$$

where $\delta\mu_0(T)$ is the shift of the Fermi surface as a function of temperature (for the one dimensional case we have $\delta\mu_0(T) = \epsilon_F(V_G) \frac{\pi^2}{12} \left(\frac{K_B T}{\epsilon_F(V_G)} \right)^2$)

For the normal order we have :

$$\begin{aligned} \langle \hat{N}_{L,\sigma}(V_G, \mu_L, T) \rangle &= \langle N_{L,\sigma}(V_G, \mu_L, T) \rangle - \langle N_{L,\sigma}(\delta\mu_0(T), T) \rangle \\ \langle \hat{N}_{R,\sigma}(V_G, \mu_R, T) \rangle &= \langle N_{R,\sigma}(V_G, \mu_R, T) \rangle - \langle N_{R,\sigma}(\delta\mu_0(T), T) \rangle \end{aligned}$$

when self energies $\delta\Sigma(V_G, l(V_G), T)$ are considered we replace : $\mu_R \rightarrow \mu_R - \delta\Sigma(V_G, l(V_G), T)$ and $\mu_L \rightarrow \mu_L - \delta\Sigma(V_G, l(V_G), T)$.

X. APPENDIX-B

The purpose of this Appendix is to compute the self energy $\delta\Sigma(V_G, l(V_G), T)$ for the following model:

$$: H_{int.}^{(n=0)}(l) := \eta_c(l(V_G)) : Q_c^2 : - \eta_s(l(V_G)) : Q_s^2 : \quad (33)$$

where $Q_c = \hat{Q}_c + \langle F|Q_c|F \rangle$ is the charge operator and $Q_s = \hat{Q}_s + \langle F|Q_s|F \rangle$ is magnetization operator. We observe the zero mode component of the hamiltonian commutes: $[H_0^{(n=0)}(l), H_{int.}^{(n=0)}(l)] = 0$ Therefore at finite temperatures the partition function $Z^{(n=0)} = T_r[e^{-\beta H^{(n=0)}(l)}]$ can be exactly computed.

Our goal is to compute the charge current $\hat{I} = e \frac{d\alpha}{dt}$ which is computed by performing the the commutator $[\alpha, H^{(n=0)}(l)]$. This commutator is independent on the magnetization operator Q_s . Therefore the only way that the magnetization can affect the charge current is trough the thermal bath. This means that the chemical potentials which enters in the reservoirs hamiltonian H_{Res} should be spin dependent. But the present model do not favor a state with finite magnetization magnetization and therefore can be ignored.

We will drop the magnetization term. Using the δ -function in its Fourier representation will allow us to compute the partition function for **the zero dimension problem with charge interactions**.

$$\begin{aligned} Z^{(n=0)} &\equiv Z_0^{(n=0)} \langle e^{-\beta H_{int.}^{(n=0)}(l)} \rangle_0 \equiv Z_0^{(n=0)} \frac{T_r[e^{-\beta H_0^{(n=0)}(l)} e^{-\beta H_{int.}^{(n=0)}(l)}]}{T_r[e^{-\beta H_0^{(n=0)}(l)}]} \\ &= \hat{Z}_0^{(n=0)} \int \frac{\beta d\lambda}{2\pi} \int d\varphi e^{i\beta\lambda\varphi} e^{-\beta\eta_c(l(V_G))\varphi^2} \langle Q_c(\delta\mu) \rangle_{\hat{0}} \end{aligned} \quad (34)$$

where $\hat{Z}_0^{(n=0)} = T_r[e^{-\beta(H_0^{(n=0)}(l) + \delta\mu Q_c)}]$ is the *shifted* non-interacting partition function . The chemical shift $\delta\mu$ will be specified later. $\langle Q_c(\delta\mu) \rangle_{\hat{0}}$ is computed using the trace with respect the shifted hamiltonian $H_0^{(n=0)}(l) + \delta\mu Q_c$.

For our purpose we will compute the partition function using the steepest decent method

for zero dimension problem. The major contribution to integral comes from the saddle point obtained by the derivative with respect λ and φ :

$$i\lambda - 2\eta_c(l(V_G))\varphi = 0 ; \quad i\varphi - i < Q_c(\delta\mu) >_{\hat{0}} = 0$$

We substitute the saddle point values, and identify:

$$\delta\Sigma(V_G, l(V_G)) \equiv \delta\mu \equiv i\lambda = 2\eta_c(l(V_G)) < Q_c(\delta\mu) >_{\hat{0}} \text{ and } < Q_c(\delta\mu) >_{\hat{0}} \equiv < G|Q_c|G >$$

With the solution for the chemical potential shift $\delta\Sigma(V_G, l(V_G))$ given by:

$$\delta\Sigma(V_G, l(V_G)) = 2\eta_c(l(V_G))4 \sum_{m=-n_F(V_G)}^{m=n_F(V_G)} f_{F.D.} \left[\frac{\epsilon(m) + \delta\Sigma(V_G, l(V_G)) - \delta\mu_0(T)}{K_B T} \right] \quad (35)$$

This equation is solved using the non interacting ground state $|F \rangle$ with the non-interacting density $n_e(V_G)$:

$$n_e(V_G) = \frac{\langle F|Q_c|F \rangle}{L} = \frac{4}{L} \sum_{m=-n_F(V_G)}^{m=n_F(V_G)} f_{F.D.} \left[\frac{\epsilon(m) - \delta\mu_0(T)}{K_B T} \right] \quad (36)$$

The solution for $\delta\Sigma(V_G, l(V_G))$ is obtained once we replace the sum by an energy integration (the density of states cancel the velocity).

$$\delta\Sigma(V_G, l(V_G)) \equiv hv_F \left[\left(\frac{1 - K_R^2(l(V_G))}{K_R^2 l(V_G)} \right) + \alpha \left(\frac{c}{v_F} \right) F \left(\frac{L}{de^{l(V_G)}}, \frac{\xi}{de^{l(V_G)}} \right) \right] \cdot \frac{n_e(V_G)}{\hat{\epsilon}(V_G, l, T, L)} \quad (37)$$

where the explicit form $\hat{\epsilon}(V_G, l, T, L)$ represents the effective dielectric function given by :

$$\hat{\epsilon}(V_G, l, T, L) = 1 + 4 \left[\frac{1 - K_R^2(l(V_G))}{K_R^2(l(V_G))} + \alpha \left(\frac{c}{v_F} \right) F \left(\frac{L}{de^{l(V_G)}}, \frac{\xi}{de^{l(V_G)}} \right) \cdot r(T) \right] \quad (38)$$

where $r(T)$ represents the thermal corrections. For the approximation: $\int_{\epsilon_F(V_G) - \delta\Sigma(V_G, l(V_G))}^{\epsilon_F(V_G) + \delta\Sigma(V_G, l(V_G))} d\epsilon f_{F.D.} \left[\frac{\epsilon - \delta\mu_0(T)}{K_B T} \right] \approx 0$ we find $r(T) = 1$ and for small values of $\delta\Sigma(V_G, l(V_G))$ we obtain : $r(T) = f_{F.D.} \left[\frac{-\epsilon_F(V_G) - \delta\mu_0(T)}{K_B T} \right] - f_{F.D.} \left[\frac{\epsilon_F(V_G) - \delta\mu_0(T)}{K_B T} \right]$.

XI. APPENDIX-C

In this appendix we will introduced the effective umklapp scattering for a lattice constant d due to the finite width. We will be interested in the effective model in the lowest band.

Due to the finite with d the transversal quantization introduces a set of discrete bands for $r \geq 1$ separated by the energy $\Delta = \frac{\hbar^2}{2m^*}(\frac{\pi}{d})^2$ The single particle energy are given by $\epsilon(n, r) = \epsilon(\hat{n}) + \Delta r^2 \equiv \epsilon(n) + \Delta(r^2 - 1)$ where $r > 1$ describes the upper bands and $\epsilon(n)$ is the energy in the lowest band $r = 1$. The electronic density operator $\rho(x)$ can be decomposed into $\rho_{<}(x)$ the density in the lowest band characterized by the short length scale d and $\rho_{>}(x)$ describes the electronic density in the higher bands $r > 1$. The full e-e interaction we can be separated into two parts the interaction in the lowest band $H_{r=1;r'=1}^{e-e}$ and the coupling between the lowest band and the rest.

$$\int dx \int dx' (\rho_{<}(x) + \rho_{>}(x)) U_{e-e}(|x - x'|) (\rho_{<}(x') + \rho_{>}(x')) = H_{r=1;r'=1}^{e-e} + H_{r=1;r'>1}^{e-e} + H_{r>1;r'>1}^{e-e} \quad (39)$$

The effective one band interaction is obtained by integrating out the upper bands with $r > 1$ and obtain the effective interaction at the scale d .

The effective one dimensional interaction for the lowest band ($r=1$) is given by:

$$H^{e-e} \approx H_{r=1;r'=1}^{e-e} + \int dx \rho_{<}(x) \varphi(x) \quad (40)$$

where $\varphi(x) = [\int dx' U_{e-e}^{(scr)}(|x - x'|) \rho_{>}(x')]$ is the effective local potential provided by the electrons in the upper band, $U_{e-e}(|x - x'|)$ is the unscreened $e - e$ interaction for the electrons in the lowest band $r = 1$ and $U_{e-e}^{(scr)}(|x - x'|)$ is the screened e-e interaction by the electrons in the higher bands $r > 1$. $\rho_{>}(x')$ is the electronic density in the upper bands $r > 1$ for which the expectation value at finite temperature is not zero $\langle \rho_{>}(x') \rangle \neq 0$.

For the one band $r = 1$ we can use the Bosonization method with the short distance cut-off d . The first term $H_{r=1;r'=1}^{e-e}$ together with the kinetic energy in the band $r = 1$ reproduces the hamiltonian in equation (2). We will show that The second term (the cosine) in equation (2) is generated by the momentum exchange with the upper bands $r > 1$. For the lowest band we can use the Bosonic representation for the density :

$$\rho_{<}(x) = \sqrt{\frac{1}{2\pi}} (\partial_x \Theta(x)) + \frac{\Lambda}{\pi} \text{Cos}[2K_F x + \sqrt{2\pi} \Theta(x) + \frac{1}{2} \hat{\alpha} + \frac{\pi}{L} \hat{Q}_c x] \text{Cos}[\sqrt{2\pi} \Theta_s(x)]$$

We observe that by summing over the spin part we find that the density depends on both the charge $\Theta(x)$ and on the spin operator $\Theta_s(x)$. We substitute the Bosonic representation of $\rho_{<}(x)$ and integrate out the spin wave operator (the effect of the $\sqrt{\frac{1}{2\pi}} (\partial_x \Theta(x))$ is negligible):

$$\begin{aligned}
H^{e-e} &\approx H_{r=1;r'=1}^{e-e} + \\
&\int dx \int dx' W(x, x') \text{Cos}[2K_F x + \sqrt{2\pi}\Theta(x) + \frac{1}{2}\hat{\alpha} + \frac{\pi}{L}\hat{Q}_c x] \text{Cos}[2K_F x + \sqrt{2\pi}\Theta(x) + \frac{1}{2}\hat{\alpha} + \frac{\pi}{L}\hat{Q}_c x'] \\
&\approx H_{r=1;r'=1}^{e-e} + g \int dx \text{Cos}[4K_F x + \sqrt{8\pi}\Theta(x) + \hat{\alpha} + \frac{2\pi}{L}\hat{Q}_c x] \dots
\end{aligned} \tag{41}$$

The second term in equation (41) represents the umklapp term introduced in equation (2) at the scale d .

Next we give the expression of the short range coupling constant $W(x, x')$ generated by the expectation value with respect the high energy bands ($r > 1, r' > 1$) and spin wave correlation function $\langle [\text{Cos}[\sqrt{2\pi}\Theta_s(x)]\text{Cos}[\sqrt{2\pi}\Theta_s(x')]] \rangle_s$ which to leading order is given by a constant .

$$\begin{aligned}
W(x, x') &= \left(\frac{\Lambda}{\pi}\right)^2 \langle \varphi(x)\varphi(x')\text{Cos}[\sqrt{2\pi}\Theta_s(x)]\text{Cos}[\sqrt{2\pi}\Theta_s(x')] \rangle = \\
&\left(\frac{\Lambda}{\pi}\right)^2 \left[\int dy \int dy' U_{e-e}^{(scr)}(|x-y|)U_{e-e}^{(scr)}(|x-y'|) \langle \rho_{>}(y)\rho_{>}(y') \rangle_{(r>1;r'>1)} \right] \cdot \\
&\langle [\text{Cos}[\sqrt{2\pi}\Theta_s(x)]\text{Cos}[\sqrt{2\pi}\Theta_s(x')]] \rangle_s \approx g
\end{aligned} \tag{42}$$

The second term in equation (41) represents the umklapp term introduced in equation (2) at the scale d .

-
- [1] H.J. Shultz Phys.Rev.Lett. **71**,1864 (1993)
 - [2] D.Schmeltzer ,Phys.Rev.B. **63** , 1253321 (2001) and Phys.Rev.Lett.**85**,4132 (2000).
 - [3] D.L. Maslov and M.Stone Phys.Rev.B **52**, R5539(1995)
 - [4] F.D.M. Haldane,J.Phys.C **14**,2585(1981) and Phys.Rev.Lett. **47**,1840(1981)
 - [5] C.L. Kane and M.P.A. Fisher Phys.Rev.B **46**,15233(1992)
 - [6] K.J. Thomas et al. Phys.Rev.Lett. **77**,135 (1996)
 - [7] R.de. Picciotto et al. Phys.Rev.B **72**,033319(2005)
 - [8] S.M. Cronennwett et al.Phys.Rev.Lett. **88**,226805(2002)
 - [9] N.Kawakami and S.K. Yang J.Phys: Condens.Matter **3**,5983(1991)
 - [10] K.Hirose et al. Phys.Rev.Lett. **90**,026804(2004)
 - [11] K.A. Matveev Phys.Rev.B **70**,245319(2004)
 - [12] J.S. Meyer and K.A. Matveev Cond-mat 0808.2076

- [13] D.Schmeltzer et al. Phys.Rev.B **71**,045429(2005) and D.Schmeltzer et al. Phys.Rev.Lett **95**,06880(2005).
- [14] D.Schmeltzer et al. Philos.Mag.B **77**,1189(1998)
- [15] Y. Yoon, L. Mourokh, T. Morimoto, N. Aoki, Y. Ochiai, J. L. Reno, and J. P. Bird **99**,136805(2007)
- [16] D.Schmeltzer, cond-matt **0211449**,v1(2002)
- [17] P.Sun and D.Schmeltzer,Phys.Rev.B ,**61**,349(2000)
- [18] R.Shankar ,Int.J.Mod.Phys.**B 4**,2371(1990)
- [19] J.M.Kosterlitz and D.Thouless, J.Phys. **C5**,L124(1972)
- [20] V.L.Berezinskii,Sov.Phys.JETP **34**,610(1972)
- [21] M.Malard, D.Schmeltzer and A.Kuklov to be published in the Proceedings of the "International Conference on Strongly Correlated Electron System" SCES(2008).
- [22] Philipe Di Francesco, Pierre Mathieu and David Senechal "Conformal Field Theory" page 390, Springer Verlag(1996)